

IN THE CLAIMS:

Please cancel claims 1-27 without prejudice, and add new claims 28-49 as follows:

1-27. (Cancelled)

28. (New) A substrate, comprising:

a first dielectric layer comprising silicon, carbon, and nitrogen; and

a second dielectric layer comprising silicon, oxygen, and carbon adjacent the first dielectric layer.

29. (New) The substrate of claim 28, further comprising:

a photoresist adjacent the second dielectric layer.

30. (New) The substrate of claim 28, further comprising:

a silicon oxide cap or nitrogen-free silicon carbide cap adjacent the second dielectric layer; and

a photoresist adjacent the silicon oxide cap or nitrogen-free silicon carbide cap.

31. (New) The substrate of claim 28, further comprising:

an etch stop adjacent the second dielectric layer; and

a third dielectric layer comprising silicon, oxygen, and carbon, adjacent the etch stop.

32. (New) The substrate of claim 31, wherein the etch stop is silicon carbide or comprises silicon, carbon, and nitrogen.

33. (New) The substrate of claim 31, further comprising:

a photoresist adjacent the third dielectric layer.

34. (New) The substrate of claim 28, wherein the first dielectric layer is adjacent a

conductive material.

35. (New) A substrate, comprising:

a first dielectric layer comprising silicon, carbon, and nitrogen, wherein the first dielectric layer is a diffusion barrier and is adjacent a conductive material;

a nitrogen free silicon carbide cap adjacent the first dielectric layer; and

a second dielectric layer comprising silicon, oxygen, and carbon adjacent the nitrogen free silicon carbide cap.

36. (New) The substrate of claim 35, further comprising:

a photoresist adjacent the second dielectric layer.

37. (New) The substrate of claim 35, further comprising:

one or more etch dielectric layers adjacent the second dielectric layer; and

a photoresist adjacent the one or more etch dielectric layers.

38. (New) The substrate of claim 37, wherein the one or more etch dielectric layers comprise a nitrogen doped silicon carbide layer adjacent the second dielectric layer.

39. (New) The substrate of claim 37, wherein the one or more etch dielectric layers comprise:

a nitrogen doped silicon carbide layer adjacent the second dielectric layer; and

nitrogen free silicon carbide cap adjacent the nitrogen doped silicon carbide layer.

40. (New) The substrate of claim 35, further comprising:

a silicon oxide cap or nitrogen-free silicon carbide cap adjacent the second dielectric layer; and

a photoresist adjacent the silicon oxide cap or nitrogen-free silicon carbide cap.

41. (New) The substrate of claim 28, further comprising:

an etch stop adjacent the second dielectric layer; and
a third dielectric layer comprising silicon, oxygen, and carbon adjacent the etch stop.

42. (New) The substrate of claim 41, wherein the etch stop comprises silicon carbide or silicon, carbon, and nitrogen.

43. (New) The substrate of claim 41, further comprising:
a photoresist adjacent the third dielectric layer.

44. (New) A substrate, comprising:
a first dielectric layer comprising silicon, carbon, and nitrogen;
a nitrogen-free silicon and carbon containing material adjacent the first dielectric layer;
a second dielectric layer comprising silicon, oxygen, and carbon on the nitrogen-free silicon and carbon containing material;
an etch stop layer adjacent the second dielectric layer; and
a photoresist adjacent the etch stop layer.

45. (New) The substrate of claim 43, further comprising:
a silicon oxide cap or nitrogen-free silicon carbide cap formed adjacent the second dielectric layer.

46. (New) The substrate of claim 45, further comprising:
a photoresist adjacent the silicon oxide cap or nitrogen-free silicon carbide cap.

47. (New) The substrate of claim 44, wherein the etch stop layer comprises a nitrogen doped silicon carbide layer.

48. (New) The substrate of claim 44, wherein the etch stop layer comprises:
a nitrogen doped silicon carbide layer adjacent the second dielectric layer; and

nitrogen free silicon carbide cap adjacent the nitrogen doped silicon carbide layer.

49. (New) The substrate of claim 44, further comprising:
a third dielectric layer comprising silicon, oxygen, and carbon, adjacent the etch stop.